

 $\ \square$ Sample Qty.

■ Test Data



SPECIFICATION FOR APPROVAL

сиѕтом	ER'S APPROVAL (СНОР	
Approval's condition: Approved date: PLEASE KINDLY RETURN A OFFICIAL STAMP ON APPR		DMPANY'S	
CUSTOMER'S NAME:			
CUSTOMER'S MODEL NO. :			
CUSTOMER'S PART NO.:			
DESCRIPTION:	Programmable	e Overvoltage Prot	ector
Semitel'S MODEL NO. :	s	SVG170DM	
VERSION:		A	
DATE:		2016/1/25	
Attachments:	Prepared By	Checked By	Approved By
☐ Product specification			

Semitel International Ltd.,	TEL: 886-2-86922121 FAX: 886-2-26483379	
IWWW semifelint com	12F, No.183, Sec.1, Datong Rd., Xizhi Dist., New Taipei City 22145, Taiwan	





Revision Record

Version	Revision Date	Revision For Items	Revision For Items
A	2016/1/25	New Revision	-
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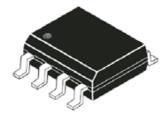
SEMITEL'S MODEL NO. :	SVG170DM	CUSTOMER'S MODEL NO. :	
VERSION:	Α	CUSTOMER'S PART NO. :	
DATE:	2016/1/25		





Description

This device is especially designed to protect subscriber line card interfaces (SLIC) against transient overvoltages. Positive overloads are clipped with 2 diodes. Negative surges are suppressed by 2 thyristors, their breakdown voltage being referenced to -VBAT through the gate. This component presents a very low gate triggering current (IGT) in order to reduce the current consumption on printed circuit board during the firing phase. A particular attention has been given to the internal wire bonding. The "4-point" configuration ensures reliable protection, eliminating the overvoltage introduced by the parasitic inductances of the wiring (Ldi/dt), especially for very fast transients.



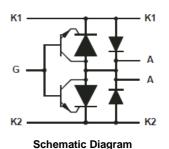
SOP-8

Features

- Dual programmable transient suppressor
- Wide battery voltage supports
- Low gate triggering current
- High holding current
- ESD Immunity(HBM): JESD22 Class 3B, ≥8KV
- MSL: Level 1 unlimited

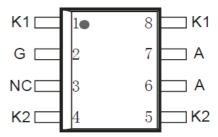
Applications

- Switch Line Card
- Access Network Line Card
- PBX
- VolP



Pin Configuration

Pin#	Pin Name	Description	
1, 4, 5, 8	K1, K2	Connect to subscriber lines (Tip/Ring)	
2	G	Connect to battery (Reference Voltage)	
6, 7	Α	Connect ground	
3	NC	Not connected	



Absolute Maximum Ratings

		,
I PP	100	А
	150	
	500	
	7.7	
Ітем	6.1	А
- 1 SIVI	4.8	A
	2.8	
	2.6	
	Ітэм	7.7 6.1 4.8 2.8

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VERSION:	Α	CUSTOMER'S PART NO. :	
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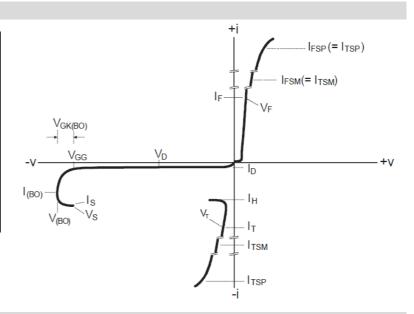




Maximum voltage LINE/GROUND	V_{DRM}	-170	V
Maximum voltage GATE/LINE	V _G KRM	-167	V
Operating free-air temperature range	TA	-40-85	°C
Storage temperature range	T _{STG}	-40-150	°C
Junction temperature	TJ	-40-150	°C
Maximum lead temperature for soldering during 10s	TL	260	°C
Junction to free air thermal resistance	Reja	120	°C /W

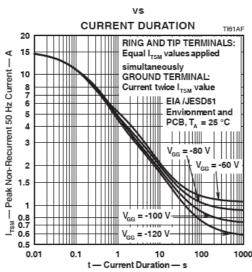
Parameter Measurement Information

Parameter	Symbol
Off-state current	I _D
Holding current	I _H
Breakover voltage	V _(BO)
Forward voltage	V_{F}
Peak forward recovery voltage	V_{FRM}
Gate-cathode impulse breakover voltage	$V_{GK(BD)}$
Gate reverse current	I _{GKS}
Gate trigger current	I _{GT}
Gate-cathode trigger voltage	V_{GT}
Cathode-anode off-state capacitance	C _{KA}



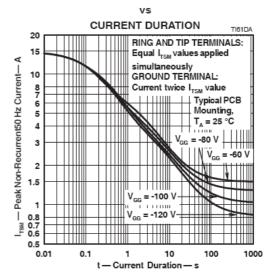
Electrical Characteristics (T_A=25°C)

PEAK NON-RECURRING AC



Non-Repetitive Peak On-State Current against Duration

TYPICAL PEAK NON-RECURRING AC



Typical Non-Repetitive Peak On-state Current against Duration

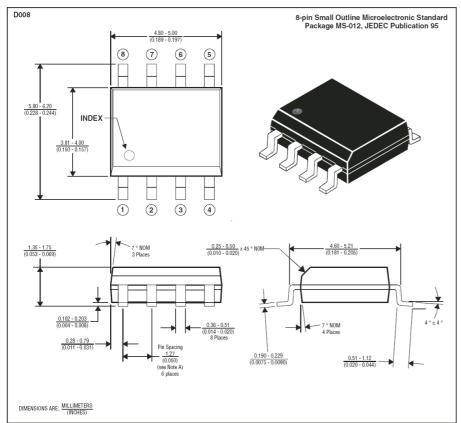
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Symbol		Symbol Test Conditions		Тур.	Max.	Unit
V_{F}	Forward voltage	I _F =5A, t _w =200μs			3	V
V_{FRM}	Peak forward recovery voltage	2/10μs, I _F =100A,Rs=50Ω, di/dt=80A/μs			10	V
I _D	Off-state current	V _D =-170V, V _{GK} =0 T _J =25°C V _D =-170V, V _{GK} =0 T _J =85°C			-5	μΑ
V _(BO)	Breakover voltage	$^{2/10}\mu s$, I_{TM} =100A, Rs=50Ω, di/dt=-80A/ μs , V_{GG} =-100V			-112	V
I _H	Holding current	I _T =-1A, di/dt=1A/ms, V _{GG} =-100V	-150			mA
I _{GAS}	Gate reverse current	V _{GG} =V _{GK} =-167V, V _{KA} =0 T _J =25°C V _{GG} =V _{GK} =-167V, V _{KA} =0 T _J =85°C			-5	μΑ
I_{GT}	Gate trigger current	I _T =3A, t _{p(g)} ≥20µs, V _{GG} =-100V			5	mA
V_{GT}	Gate trigger voltage	I _T =3A, t _{p(g)} ≥20µs, V _{GG} =-100V			2.5	V
Ска	Anode-cathode offstate capacitance	f=1MHz,V _d =1V, I _G =0 V _D =-3V f=1MHz,V _d =1V, I _G =0 V _D =-48V			110 55	pF

Product Dimension



NOTES:

A. Leads are within 0.25 (0.010) radius of true position at maximum material condition.

- B. Body dimensions do not include mold flash or protrusion.
- C. Mold flash or protrusion shall not exceed 0.15 (0.006).
- D. Lead tips to be planar within ± 0.051 (0.002).

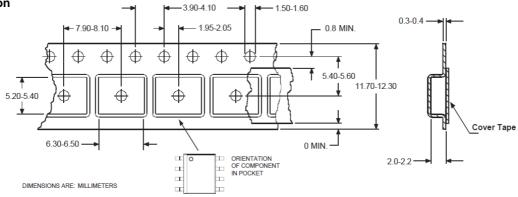
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Package Information

Tape Dimension



NOTES: A. Taped devices are supplied on a reel of the following dimensions:-

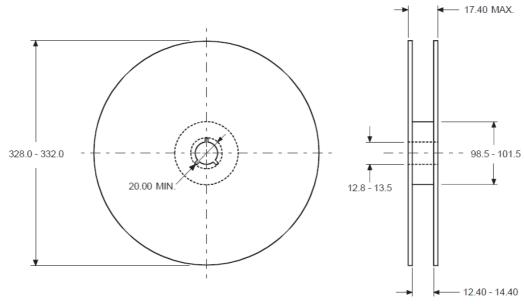
Reel diameter: $\frac{330 + 0.0/-4.0}{(12.992 + 0.0/-.157)}$

Reel hub diameter : $\frac{100 \pm 2.0}{(3.937 \pm .079)}$

Reel axial hole: $\frac{13.0 \pm 0.2}{(.512 \pm .008)}$

B. 2500 devices are on a reel.

Reel Dimension



DIMENSIONS ARE: MILLIMETERS

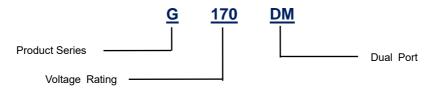
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DATE:	2016/1/25		





Marking and Order Information

Part Number System



Order Information

Device	Package	Net Weight	Carrier	Quantity	HSF Status
G170DM	SOP-8	0.080g	Tape & Reel	2,500pcs/reel	RoHS compliant

Marking



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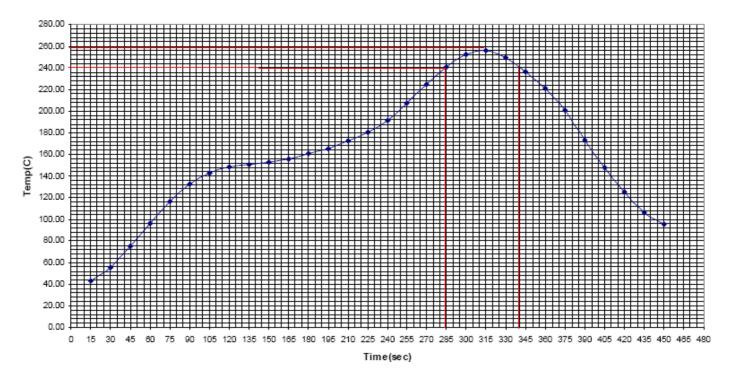




Reflow Soldering and Rework Recommendations

- Recommended reflow methods, Recommended reflow methods: IR, Vapor phase oven, hot air oven, wave solder.
- Devices can be cleaned using standard industry methods and solvents.
- If a device is removed from the board, it should be discarded and replaced with a new device.
- Leaded devices are not designed to be compatible with wave soldering manufacturing operations.
- Lead free reflow curve.

Peak Temp=257C, Ramp Rate=0.802deg.C/sec.



SEMITEL'S MODEL NO. :	SVG170DM	CUSTOMER'S MODEL NO. :	
VERSION:	Α	CUSTOMER'S PART NO. :	
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